


"High Side Chopper" IGBT SOT-227 (Trench IGBT), 100 A



SOT-227

PRODUCT SUMMARY	
V_{CES}	1200 V
I_C DC	100 A at 71 °C
$V_{CE(on)}$ typical at 100 A, 25 °C	2.45 V
Package	SOT-227
Circuit	High side switch

FEATURES

- Trench IGBT technology
- Very low $V_{CE(on)}$
- Square RBSOA
- HEXFRED® clamping diode
- 10 μ s short circuit capability
- Fully isolated package
- Speed 4 kHz to 30 kHz
- Very low internal inductance (≤ 5 nH typical)
- Industry standard outline
- UL approved file E78996 
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


**RoHS
COMPLIANT**

BENEFITS

- Designed for increased operating efficiency in power conversion: UPS, SMPS, welding, induction heating
- Easy to assemble and parallel
- Direct mounting on heatsink
- Plug-in compatible with other SOT-227 packages
- Low EMI, requires less snubbing

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Collector to emitter voltage	V_{CES}		1200	V
Continuous collector current	I_C	$T_C = 25\text{ °C}$	134	A
		$T_C = 80\text{ °C}$	92	
Pulsed collector current	I_{CM}		270	
Clamped inductive load current	I_{LM}		270	
Diode continuous forward current	I_F	$T_C = 25\text{ °C}$	87	
		$T_C = 80\text{ °C}$	59	
Single pulse forward current	I_{FSM}	10 ms sine or 6 ms rectangular pulse, $T_J = 25\text{ °C}$	360	
Gate to emitter voltage	V_{GE}		± 30	V
Power dissipation, IGBT	P_D	$T_C = 25\text{ °C}$	463	W
		$T_C = 80\text{ °C}$	260	
Power dissipation, diode	P_D	$T_C = 25\text{ °C}$	338	
		$T_C = 80\text{ °C}$	190	
RMS isolation voltage	V_{ISOL}	Any terminal to case, $t = 1$ min	2500	V



ELECTRICAL SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Collector to emitter breakdown voltage	$V_{BR(CE)}$	$V_{GE} = 0\text{ V}, I_C = 250\text{ }\mu\text{A}$	1200	-	-	V
Collector to emitter voltage	$V_{CE(on)}$	$V_{GE} = 15\text{ V}, I_C = 50\text{ A}$	-	1.73	2.33	
		$V_{GE} = 15\text{ V}, I_C = 100\text{ A}$	-	2.26	-	
		$V_{GE} = 15\text{ V}, I_C = 50\text{ A}, T_J = 125\text{ }^\circ\text{C}$	-	2.02	-	
		$V_{GE} = 15\text{ V}, I_C = 100\text{ A}, T_J = 125\text{ }^\circ\text{C}$	-	2.77	-	
Gate threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}, I_C = 3.5\text{ mA}$	4.6	5.8	8.0	
Temperature coefficient of threshold voltage	$V_{GE(th)}/\Delta T_J$	$V_{CE} = V_{GE}, I_C = 3.5\text{ mA}$ ($25\text{ }^\circ\text{C}$ to $125\text{ }^\circ\text{C}$)	-	-14.5	-	mV/ $^\circ\text{C}$
Collector to emitter leakage current	I_{CES}	$V_{GE} = 0\text{ V}, V_{CE} = 1200\text{ V}$	-	0.5	75	μA
		$V_{GE} = 0\text{ V}, V_{CE} = 1200\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	0.12	-	mA
Diode reverse breakdown voltage	V_{BR}	$I_R = 1\text{ mA}$	1200	-	-	V
Diode forward voltage drop	V_{FM}	$I_F = 50\text{ A}, V_{GE} = 0\text{ V}$	-	2.65	3.55	V
		$I_F = 100\text{ A}, V_{GE} = 0\text{ V}$	-	3.5	-	
		$I_F = 50\text{ A}, V_{GE} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	2.82	-	
		$I_F = 100\text{ A}, V_{GE} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	3.9	-	
Diode reverse leakage current	I_{RM}	$V_R = 1200\text{ V}$	-	4	50	μA
		$T_J = 125\text{ }^\circ\text{C}, V_R = 1200\text{ V}$	-	0.8	-	mA
Gate to emitter leakage current	I_{GES}	$V_{GE} = \pm 30\text{ V}$	-	-	± 600	nA

SWITCHING CHARACTERISTICS ($T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Total gate charge (turn-on)	Q_g	$I_C = 100\text{ A}, V_{CC} = 600\text{ V}, V_{GE} = 15\text{ V}$	-	400	-	nC
Gate to emitter charge (turn-on)	Q_{ge}		-	120	-	
Gate to collector charge (turn-on)	Q_{gc}		-	170	-	
Turn-on switching loss	E_{on}	$I_C = 100\text{ A}, V_{CC} = 600\text{ V}, V_{GE} = 15\text{ V}, R_g = 2.2\text{ }\Omega, L = 500\text{ }\mu\text{H}$	-	4.76	-	mJ
Turn-off switching loss	E_{off}		-	3.64	-	
Total switching loss	E_{tot}		-	8.4	-	
Turn-on switching loss	E_{on}		-	6.88	-	
Turn-off switching loss	E_{off}		-	5.66	-	
Total switching loss	E_{tot}		-	12.54	-	
Turn-on delay time	$t_{d(on)}$		$I_C = 100\text{ A}, V_{CC} = 600\text{ V}, V_{GE} = 15\text{ V}, R_g = 2.2\text{ }\Omega, L = 500\text{ }\mu\text{H}, T_J = 125\text{ }^\circ\text{C}$	-	150	
Rise time	t_r	-		55	-	
Turn-off delay time	$t_{d(off)}$	-		164	-	
Fall time	t_f	-		167	-	
Reverse bias safe operating area	RBSOA	$T_J = 150\text{ }^\circ\text{C}, I_C = 270\text{ A}, R_g = 22\text{ }\Omega, V_{GE} = 15\text{ V to } 0\text{ V}, V_{CC} = 900\text{ V}, V_P = 1200\text{ V}$	Fullsquare			
Short circuit safe operating area	SCSOA	$T_J = 150\text{ }^\circ\text{C}, R_g = 22\text{ }\Omega, V_{GE} = 15\text{ V to } 0\text{ V}, V_{CC} = 900\text{ V}, V_P = 1200\text{ V}$	10			μs
Diode reverse recovery time	t_{rr}	$I_F = 50\text{ A}, di_F/dt = 200\text{ A}/\mu\text{s}, V_R = 200\text{ V}$	-	129	-	ns
Diode peak reverse current	I_{rr}		-	11	-	A
Diode recovery charge	Q_{rr}		-	710	-	nC
Diode reverse recovery time	t_{rr}	$I_F = 50\text{ A}, di_F/dt = 200\text{ A}/\mu\text{s}, V_R = 200\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	208	-	ns
Diode peak reverse current	I_{rr}		-	17	-	A
Diode recovery charge	Q_{rr}		-	1768	-	nC



THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL		MIN.	TYP.	MAX.	UNITS
Junction and storage temperature range	T_J, T_{Stg}		-40	-	150	°C
Junction to case	IGBT	R_{thJC}	-	-	0.27	°C/W
	Diode		-	-	0.37	
Case to heatsink	R_{thCS}	Flat, greased surface	-	0.05	-	
Weight			-	30	-	g
Mounting torque			-	-	1.3	Nm
Case style	SOT-227					

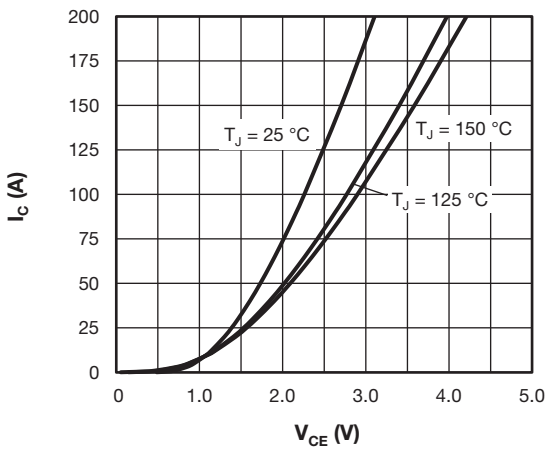


Fig. 1 - Typical IGBT Output Characteristics, $V_{GE} = 15\text{ V}$

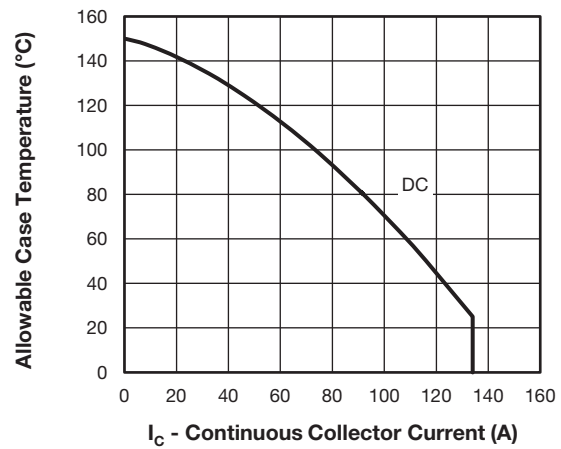


Fig. 3 - Maximum IGBT Continuous Collector Current vs. Case Temperature

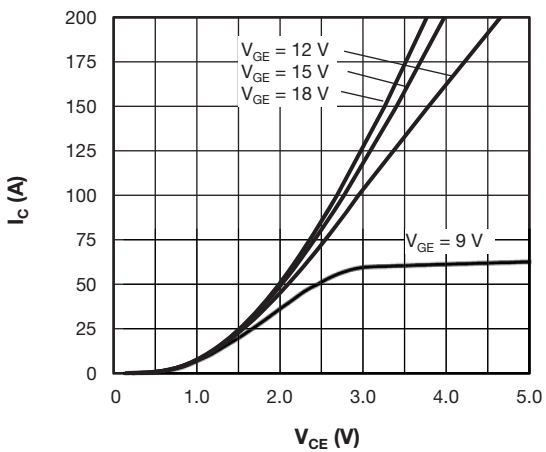


Fig. 2 - Typical IGBT Output Characteristics, $T_J = 125\text{ °C}$

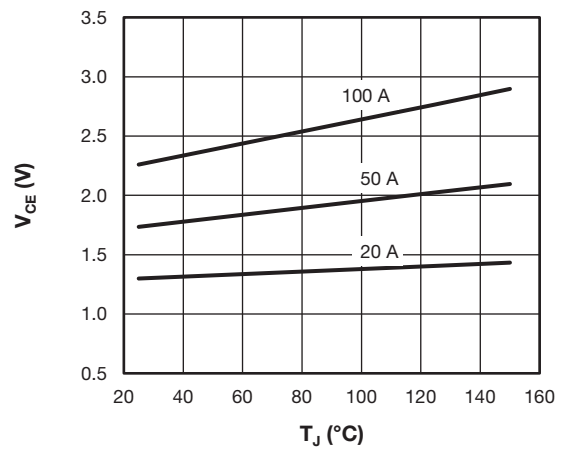


Fig. 4 - Collector to Emitter Voltage vs. Junction Temperature

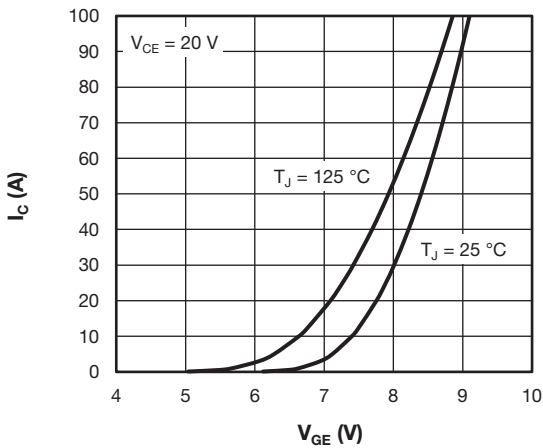


Fig. 5 - Typical IGBT Transfer Characteristics

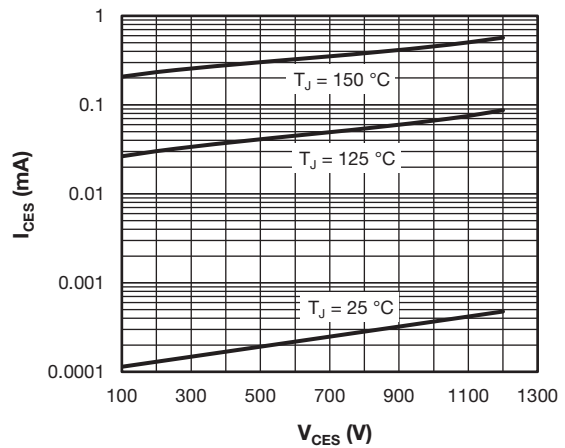


Fig. 8 - Typical IGBT Zero Gate Voltage Collector Current

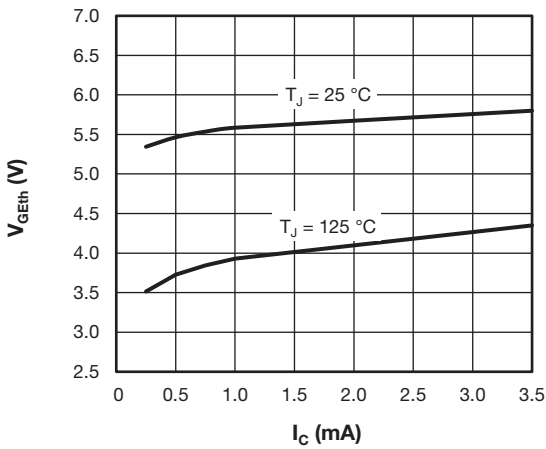


Fig. 6 - Typical IGBT Gate Threshold Voltage

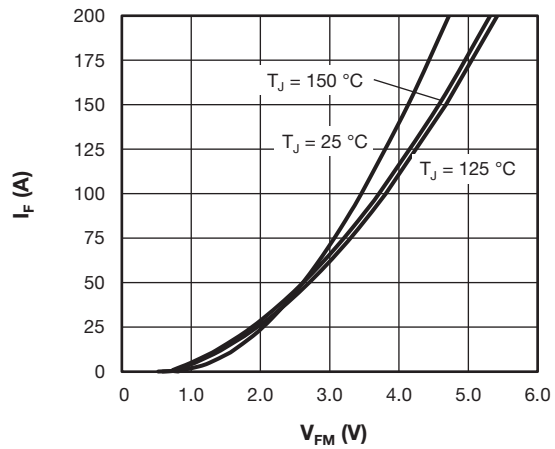


Fig. 9 - Typical Diode Forward Characteristics

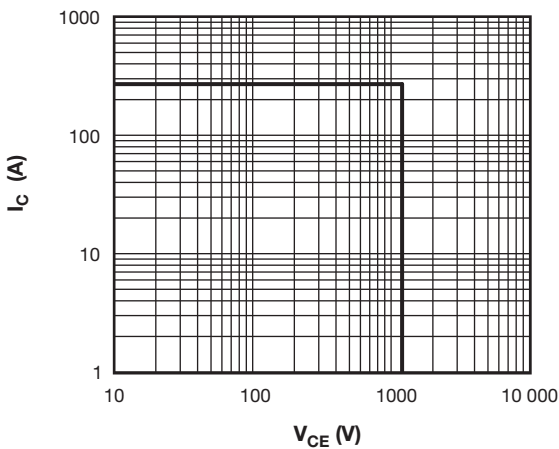


Fig. 7 - IGBT Reverse Bias SOA $T_J = 150\text{ }^\circ\text{C}$, $V_{GE} = 15\text{ V}$

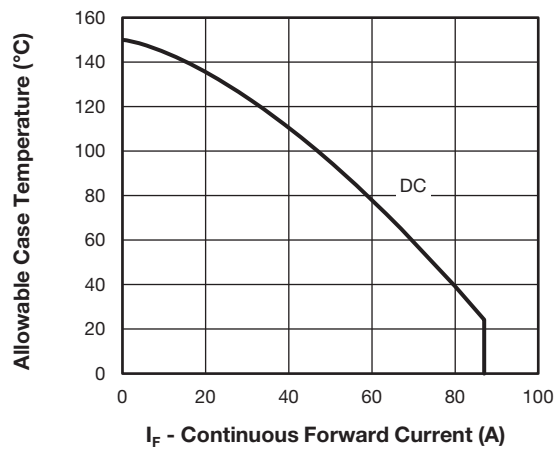


Fig. 10 - Maximum Diode Continuous Forward Current vs. Case Temperature

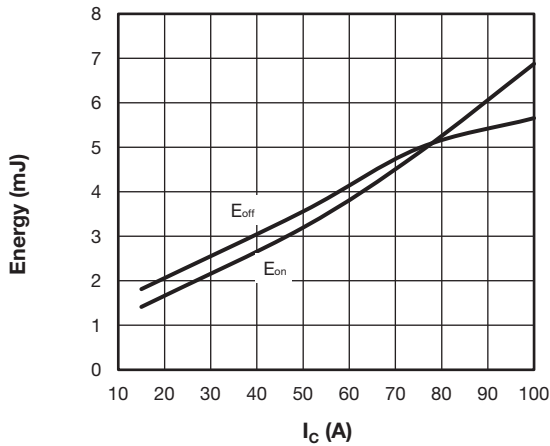


Fig. 11 - Typical IGBT Energy Loss vs. I_C
 $T_J = 125^\circ\text{C}$, $V_{CC} = 600\text{ V}$, $R_g = 2.2\ \Omega$, $V_{GE} = 15\text{ V}$, $L = 500\ \mu\text{H}$

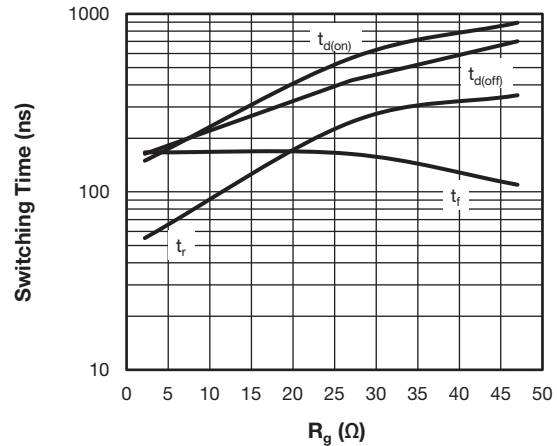


Fig. 14 - Typical IGBT Switching Time vs. R_g
 $T_J = 125^\circ\text{C}$, $V_{CC} = 600\text{ V}$, $I_C = 100\text{ A}$, $V_{GE} = 15\text{ V}$, $L = 500\ \mu\text{H}$

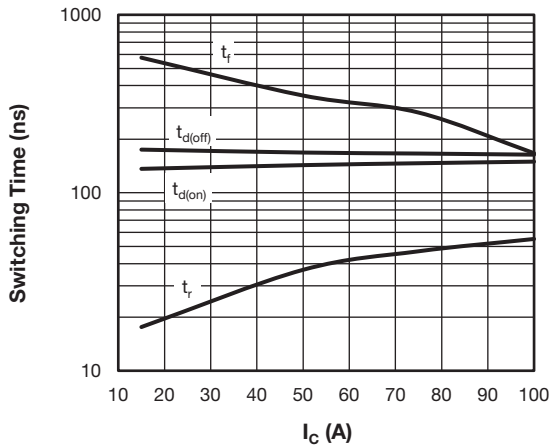


Fig. 12 - Typical IGBT Switching Time vs. I_C
 $T_J = 125^\circ\text{C}$, $V_{CC} = 600\text{ V}$, $R_g = 2.2\ \Omega$, $V_{GE} = 15\text{ V}$, $L = 500\ \mu\text{H}$

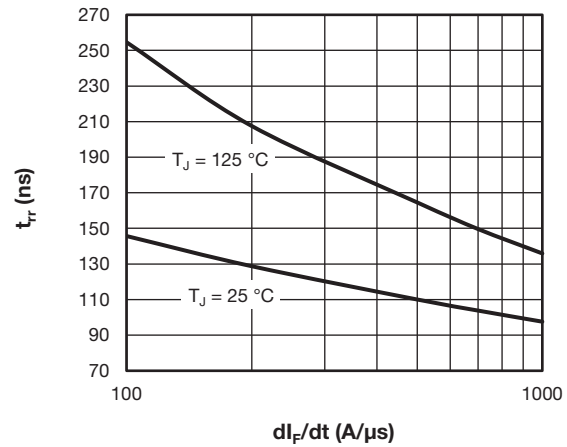


Fig. 15 - Typical Diode Reverse Recovery Time vs. dI_F/dt
 $V_{rr} = 200\text{ V}$, $I_F = 50\text{ A}$

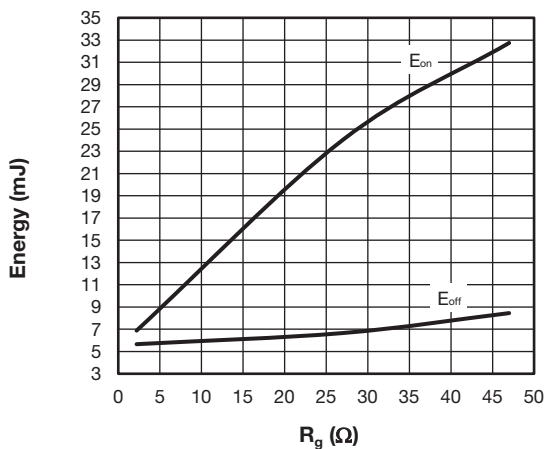


Fig. 13 - Typical IGBT Energy Loss vs. R_g
 $T_J = 125^\circ\text{C}$, $V_{CC} = 600\text{ V}$, $I_C = 100\text{ A}$, $V_{GE} = 15\text{ V}$, $L = 500\ \mu\text{H}$

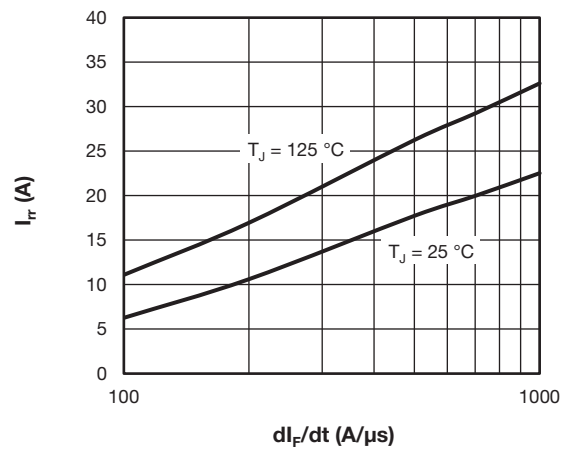


Fig. 16 - Typical Diode Reverse Recovery Current vs. dI_F/dt
 $V_{rr} = 200\text{ V}$, $I_F = 50\text{ A}$

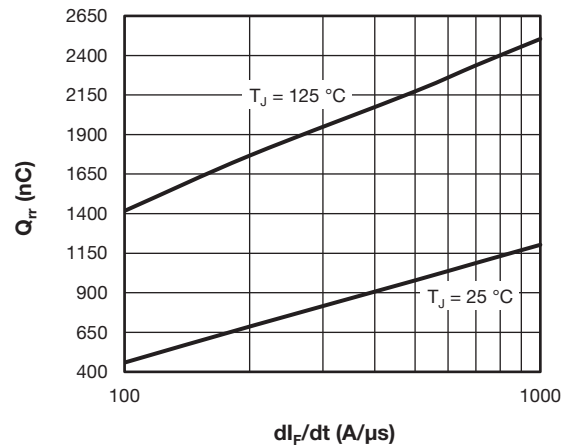


Fig. 17 - Typical Diode Reverse Recovery Charge vs. di_F/dt
 $V_{rr} = 200\text{ V}$, $I_F = 50\text{ A}$

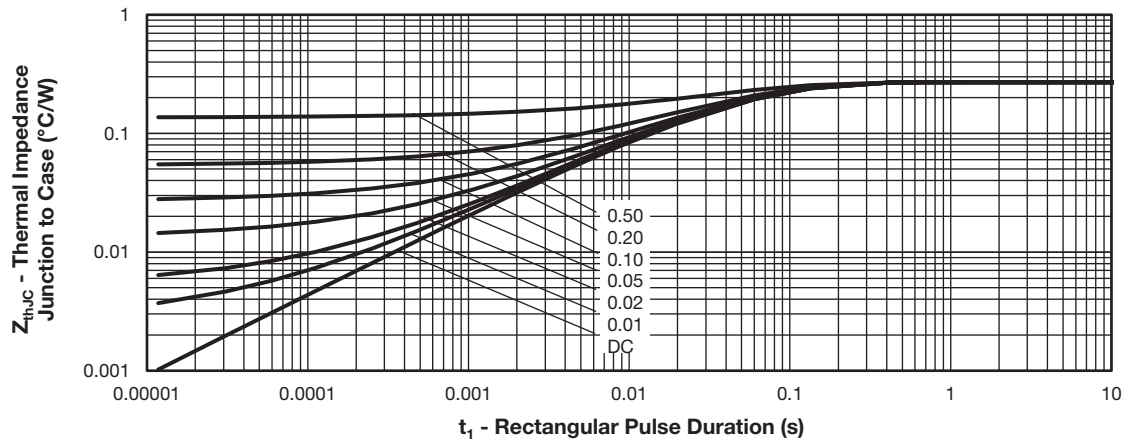


Fig. 18 - Maximum Thermal Impedance Z_{thJC} Characteristics - (IGBT)

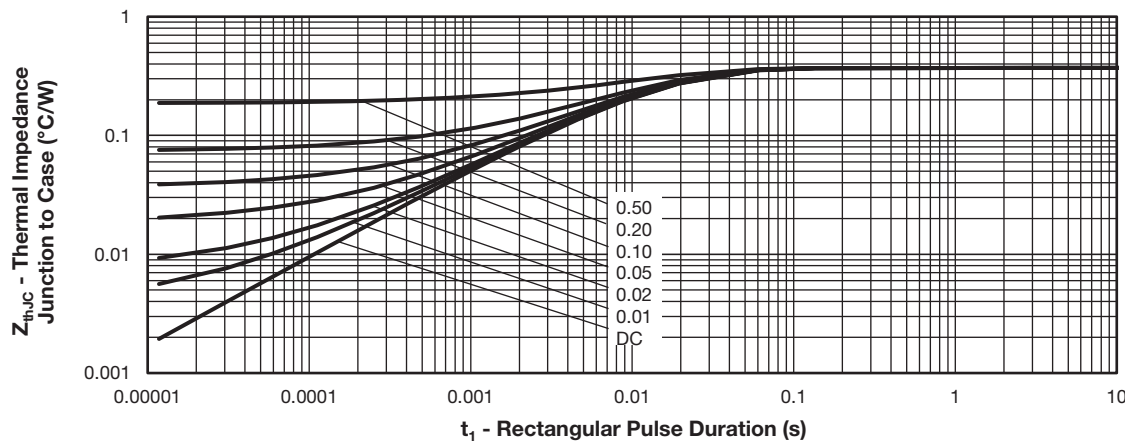


Fig. 19 - Maximum Thermal Impedance Z_{thJC} Characteristics - (Diode)



ORDERING INFORMATION TABLE

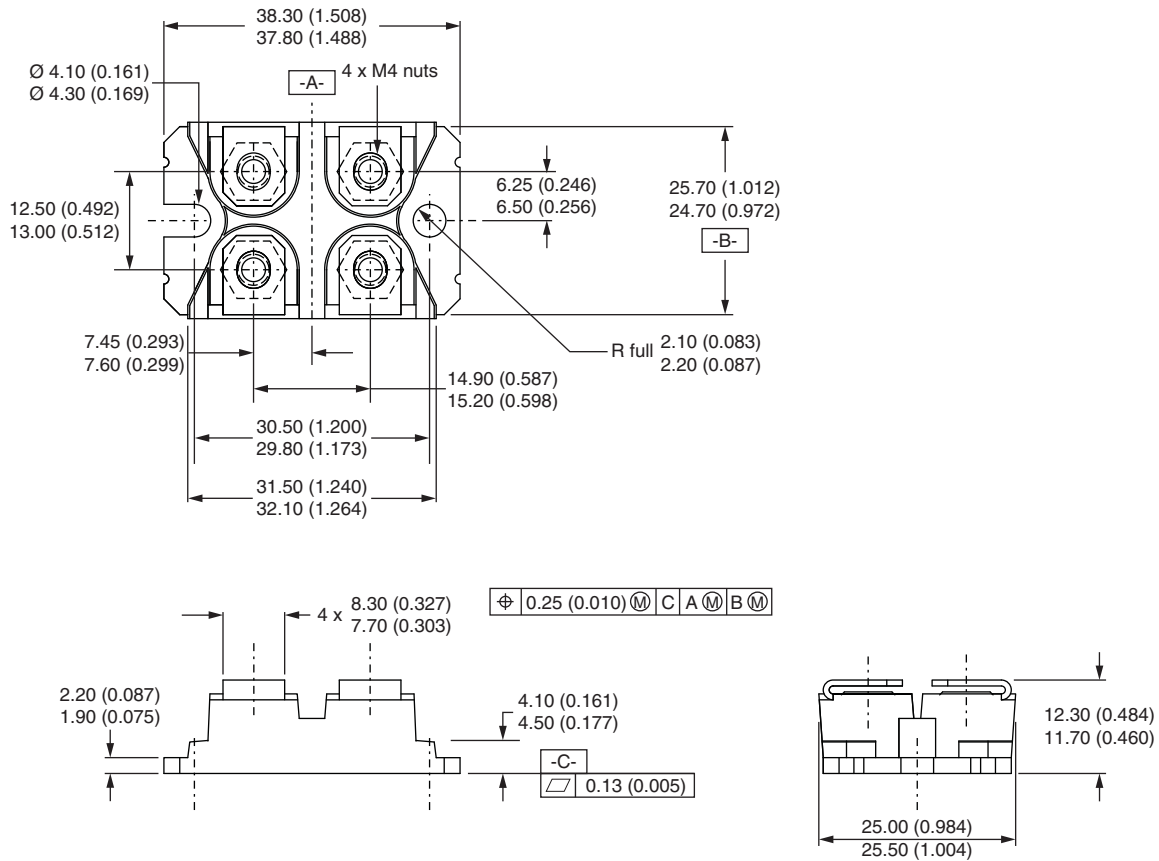
Device code	VS-	G	T	105	N	A	120	U	X
	1	2	3	4	5	6	7	8	9

- 1** - Vishay Semiconductors product
- 2** - Insulated Gate Bipolar Transistor (IGBT)
- 3** - T = Trench IGBT
- 4** - Current rating (105 = 100 A)
- 5** - Circuit configuration (N = High side chopper)
- 6** - Package indicator (A = SOT-227)
- 7** - Voltage rating (120 = 1200 V)
- 8** - Speed/type (U = Ultrafast IGBT)
- 9** - Diode (X = HEXFRED®)

CIRCUIT CONFIGURATION		
CIRCUIT	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING
High side chopper IGBT	N	



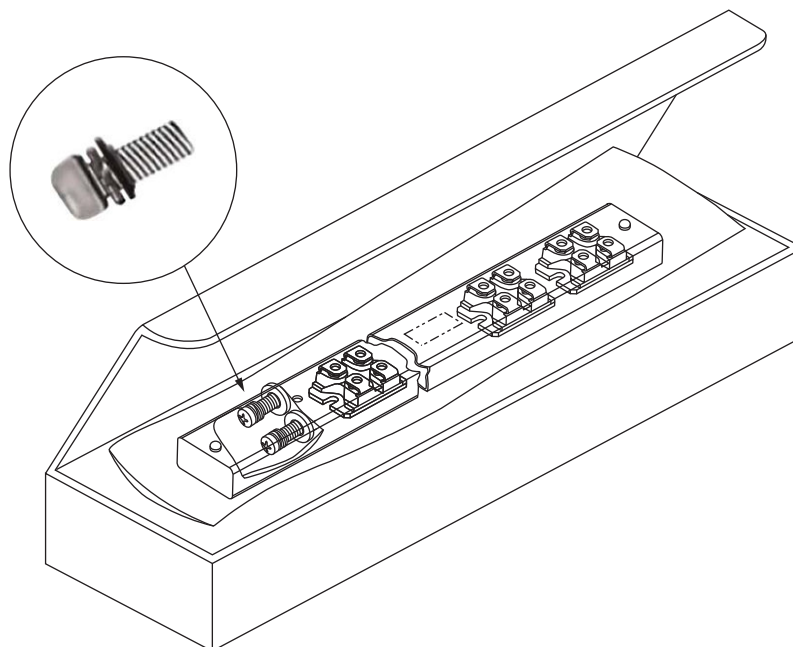
DIMENSIONS in millimeters (inches)



Note

- Controlling dimension: millimeter

PACKAGING INFORMATION SOT-227 GENERATION II





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